# onsemi

## **MOSFET** - Power, Single P-Channel, SOT-23

### -60 V, 230 mΩ, -1.1 A

## NVR5124PL

#### Features

- Trench Technology
- NVR Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Paran	Symbol	Value	Unit		
Drain-to-Source Voltag	V <sub>DSS</sub>	-60	V		
Gate-to-Source Voltage	V <sub>GS</sub>	±20	V		
Continuous Drain	Steady State	T <sub>A</sub> = 25°C	۱ <sub>D</sub>	-1.1	А
Current R <sub>θJA</sub> (Notes 1, 2, 3)	Sidle	T <sub>A</sub> = 100°C		-0.67	
Power Dissipation		$T_A = 25^{\circ}C$	PD	0.47	W
$R_{\theta JA}$ (Notes 1, 2)		0.19			
Pulsed Drain Current	Pulsed Drain Current $T_A = 25^{\circ}C$ , $t_p = 10 \ \mu s$			25	А
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C
Source Current (Body Diode)			۱ <sub>S</sub>	-0.6	А
Lead Temperature for Se (1/8" from case for 10 s)		urposes	ΤL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

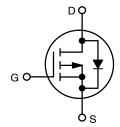
Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	268	°C/W

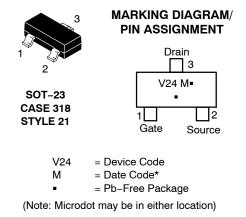
 The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
 Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.

 Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub> MAX	
–60 V	230 mΩ @ –10 V	-1.1 A	
-60 V	365 mΩ @ −4.5 V	-1.1 A	







\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NVR5124PLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

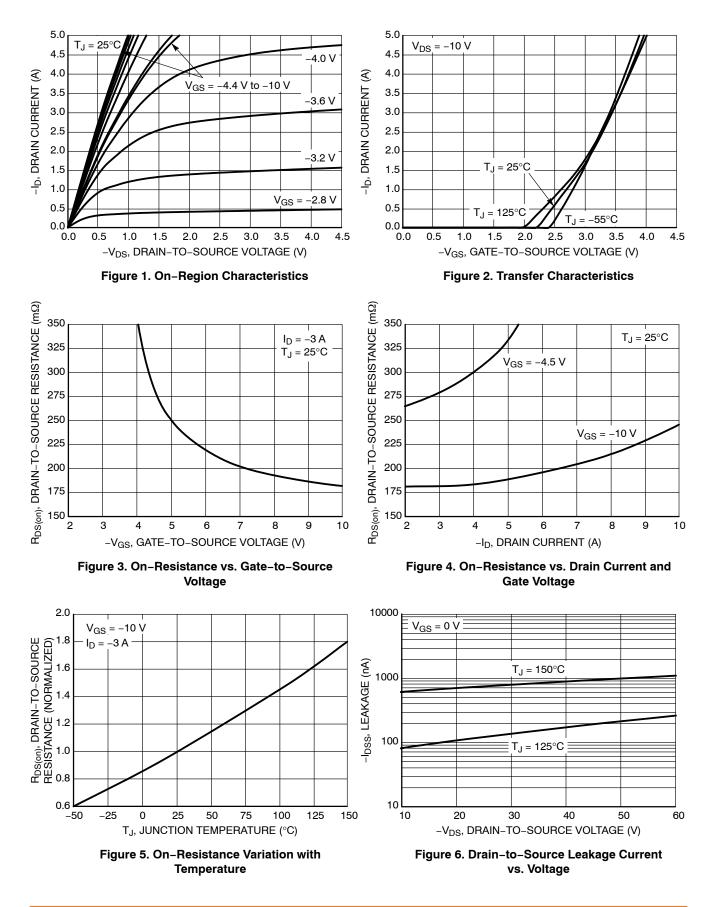
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

#### ELECTRICAL CHARACTERISTICS (T<sub>.1</sub> = 25°C unless otherwise noted)

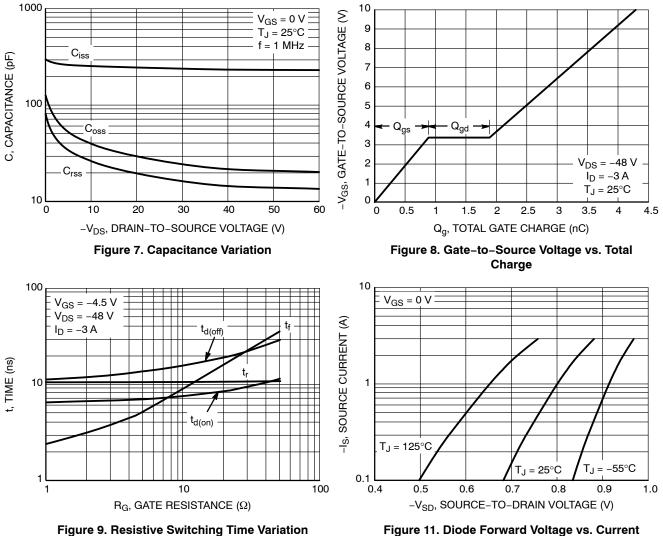
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS					•		-
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V, I_D =$	= –250 μA	-60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V,$	$T_J = 25^{\circ}C$	-	-	-1.0	μA
		V <sub>DS</sub> = -60 V	T <sub>J</sub> = 125°C	_	-	-10	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS}$	<sub>S</sub> = ±20 V	_	-	$\pm100$	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D$	= –250 μA	-1.5	-	-2.5	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V,	I <sub>D</sub> = -3 A	-	183	230	mΩ
		V <sub>GS</sub> = -4.5 V,	I <sub>D</sub> = -3 A	-	280	365	
Forward Transconductance	9 <sub>FS</sub>	V <sub>DS</sub> = -15 V,	I <sub>D</sub> = -5 A	4	-	_	S
CHARGES AND CAPACITANCES							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, f =		-	240	-	pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -2	25 V	_	27.6	_	
Reverse Transfer Capacitance	C <sub>rss</sub>			_	18.5	_	
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{GS} = -4.5 V, V$	<sub>DS</sub> = -48 V,	-	2.3	-	nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	I <sub>D</sub> = -3	5 A	_	0.5	_	
Gate-to-Source Charge	Q <sub>GS</sub>			_	0.9	_	
Gate-to-Drain Charge	Q <sub>GD</sub>			_	1.0	_	
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = -10 V, V <sub>I</sub> I <sub>D</sub> = -3	DS = −48 V, 3 A	_	4.3	-	
SWITCHING CHARACTERISTICS (No	e 5)						
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{GS} = -4.5 V, V$	<sub>DS</sub> = -48 V,	_	6.6	-	ns
Rise Time	t <sub>r</sub>	$I_{\rm D} = -3$ A, $R_{\rm G} = 2.5 \Omega$		_	10.6	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			_	12.2	-	
Fall Time	t <sub>f</sub>			-	3.5	-	
DRAIN-SOURCE DIODE CHARACTER	ISTICS				-		-
Forward Diode Voltage	V <sub>SD</sub>	$V_{GS} = 0 V,$	$T_J = 25^{\circ}C$	-	-0.88	-1.0	V
		$I_{\rm S} = -3 {\rm A}$ $T_{\rm J} = 125^{\circ}{\rm C}$		_	-0.76	_	1
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0		-	15	-	ns
Charge Time	t <sub>a</sub>	dl <sub>S</sub> /dt = 10 I <sub>S</sub> = -3	0 Α/μs, 8 Α	-	13	-	1
Discharge Time	t <sub>b</sub>	č		_	2.4	-	1
Reverse Recovery Charge	Q <sub>RR</sub>			_	10	_	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
4. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

#### **TYPICAL CHARACTERISTICS**

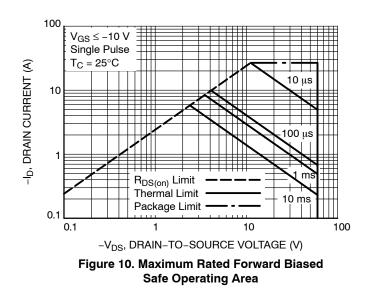


#### **TYPICAL CHARACTERISTICS**



vs. Gate Resistance

Figure 11. Diode Forward Voltage vs. Current



www.onsemi.com 4

#### **TYPICAL CHARACTERISTICS**

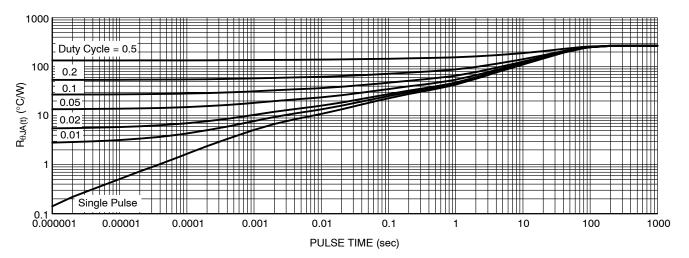


Figure 12. Thermal Response

## semi



#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

**ISSUE AU** 

DATE 14 AUG 2024













XXX = Specific Device Code М = Date Code

= Pb-Free Package .

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MILLIMETERS						
DIM	MIN	NOM	МАХ			
А	0.89	1.00	1.11			
A1	0.01	0.06	0.10			
b	0.37	0.44	0.50			
с	0.08	0.14	0.20			
D	2.80	2.90	3.04			
E	1.20	1.30	1.40			
е	1.78	1.90	2.04			
L	0.30	0.43	0.55			
L1	0.35	0.54	0.69			
Ηe	2.10	2.40	2.64			
Т	0°		10°			

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER: 98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION: SOT-23 (TO-236) 2.90x1.30x1.00 1.90P PAGE 1 OF 2					
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.					

#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CÁSE 318** ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DESCRIPTION: SOT-23 (TO-236) 2.90x1.30x1.00 1.90P PAGE 2 OF 2	DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED	
	DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 2 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent\_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>